

STANDARD RECOVERY DIODES

Stud Version

Features

- High surge current capability
- Avalanche types available
- Stud cathode and stud anode version
- Wide current range
- Types up to 1200V V_{RRM}

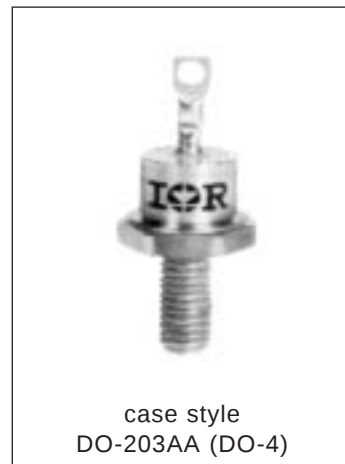
12 A

Typical Applications

- Battery charges
- Converters
- Power supplies
- Machine tool controls

Major Ratings and Characteristics

Parameters		12F(R)	Units
$I_{F(AV)}$		12	A
	@ T_C	144	°C
$I_{F(RMS)}$		19	A
I_{FSM}	@ 50Hz	265	A
	@ 60Hz	280	A
I^2t	@ 50Hz	351	A ² s
	@ 60Hz	320	A ² s
V_{RRM}	range	100 to 1200	V
T_J	range	- 65 to 175	°C



12F(R) Series

Bulletin I20205 rev. A 09/98

International
IOR Rectifier

ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{RRM} , maximum repetitive peak reverse voltage V	V_{RSM} , maximum non-repetitive peak reverse voltage V	$V_{R(BR)}$, minimum avalanche voltage V (1)	I_{RRM} max. @ $T_J = 175^\circ\text{C}$ mA
12F(R)	10	100	150	--	12
	20	200	275	--	
	40	400	500	500	
	60	600	725	750	
	80	800	950	950	
	100	1000	1200	1150	
	120	1200	1400	1350	

(1) Avalanche version only available from V_{RRM} 400V to 1200V.

Forward Conduction

Parameter	12F(R)	Units	Conditions
$I_{F(AV)}$ Max. average forward current @ Case temperature	12 144	A $^\circ\text{C}$	180° conduction, half sine wave
$I_{F(RMS)}$ Max. RMS forward current	19	A	
P_R Maximum non-repetitive peak reverse power	7	K/W	10μs square pulse, $T_J = T_J$ max. see note (2)
I_{FSM} Max. peak, one-cycle forward, non-repetitive surge current	265	A	t = 10ms No voltage
	280		t = 8.3ms reappplied
	225		t = 10ms 100% V_{RRM}
	235		t = 8.3ms reappplied
I^2t Maximum I^2t for fusing	351	A^2s	t = 10ms No voltage
	320		t = 8.3ms reappplied
	250		t = 10ms 100% V_{RRM}
	226		t = 8.3ms reappplied
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	3510	$\text{A}^2\sqrt{\text{s}}$	t = 0.1 to 10ms, no voltage reappplied
$V_{F(TO)1}$ Low level value of threshold voltage	0.77	V	$(16.7\% \times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)}), T_J = T_J$ max.
$V_{F(TO)2}$ High level value of threshold voltage	0.97		$(I > \pi \times I_{F(AV)}), T_J = T_J$ max.
r_{f1} Low level value of forward slope resistance	10.70	mΩ	$(16.7\% \times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)}), T_J = T_J$ max.
r_{f2} High level value of forward slope resistance	6.20		$(I > \pi \times I_{F(AV)}), T_J = T_J$ max.
V_{FM} Max. forward voltage drop	1.26	V	$I_{pk} = 38\text{A}, T_J = 25^\circ\text{C}, t_p = 400\mu\text{s}$ rectangular wave

(2) Available only for Avalanche version, all other parameters the same as 12F.

Thermal and Mechanical Specifications

Parameter	12F(R)	Units	Conditions
T_J Max. junction operating temperature range	-65 to 175	°C	
T_{stg} Max. storage temperature range	-65 to 200		
R_{thJC} Max. thermal resistance, junction to case	2	K/W	DC operation
R_{thCS} Max. thermal resistance, case to heatsink	0.5		Mounting surface, smooth, flat and greased
T Mounting torque, $\pm 10\%$	1.2 (1.5)	Nm	Lubricated threads (Not lubricated threads)
wt Approximate weight	7 (0.25)	g (oz)	
Case style	DO-203AA (DO-4)		See Outline Table

ΔR_{thJC} Conduction

(The following table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction	Rectangular conduction	Units	Conditions
180°	0.33	0.26	K/W	$T_J = T_{J \text{ max.}}$
120°	0.41	0.44		
90°	0.53	0.58		
60°	0.78	0.81		
30°	1.28	1.29		

Ordering Information Table

Device Code

Digit	Code
1	A
2	12
3	F
4	R
5	120
6	M

- 1** - A = Avalanche diode
None = Standard diode
- 2** - Current rating: Code = $I_{F(AV)}$
- 3** - F = Standard device
- 4** - None = Stud Normal Polarity (Cathode to Stud)
R = Stud Reverse Polarity (Anode to Stud)
- 5** - Voltage code: Code x 10 = V_{RRM} (See Voltage Ratings table)
- 6** - None = Stud base DO-203AA (DO-4) 10-32UNF-2A
M = Stud base DO-203AA (DO-4) M5 X 0.8 - (Not available for Avalanche diodes)

12F(R) Series

Bulletin I20205 rev. A 09/98

Outlines Table

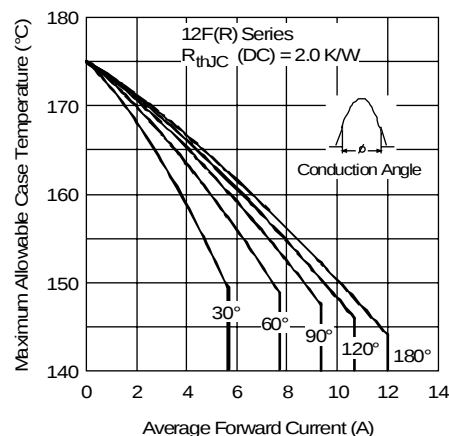
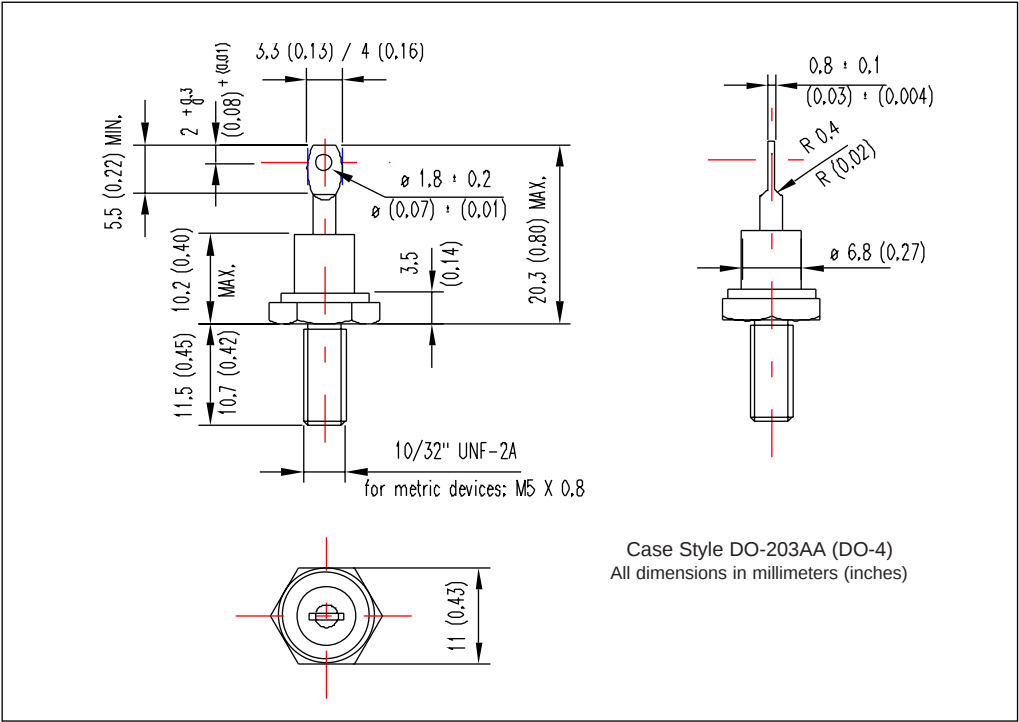


Fig. 1 - Current Ratings Characteristics

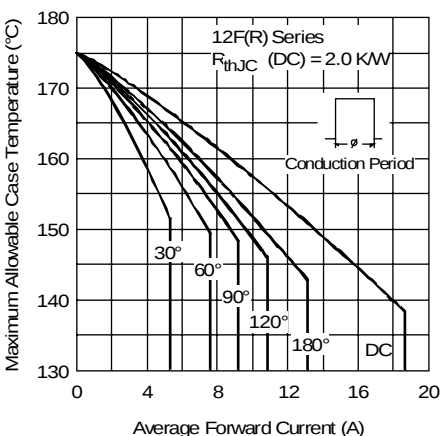


Fig. 2 - Current Ratings Characteristics

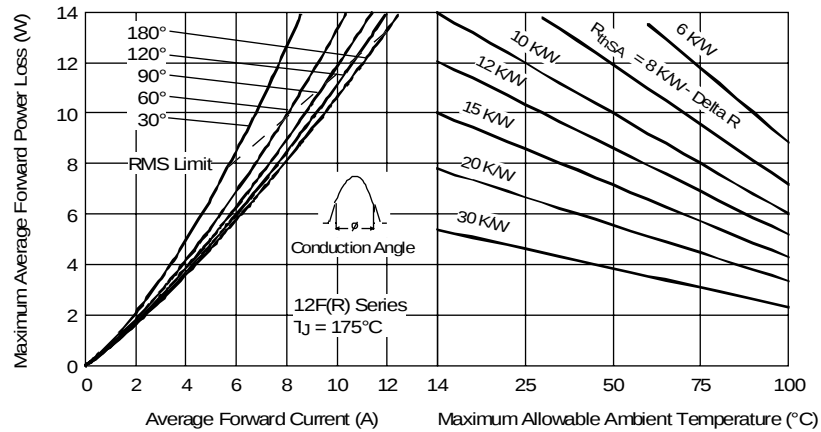


Fig. 3 - Forward Power Loss Characteristics

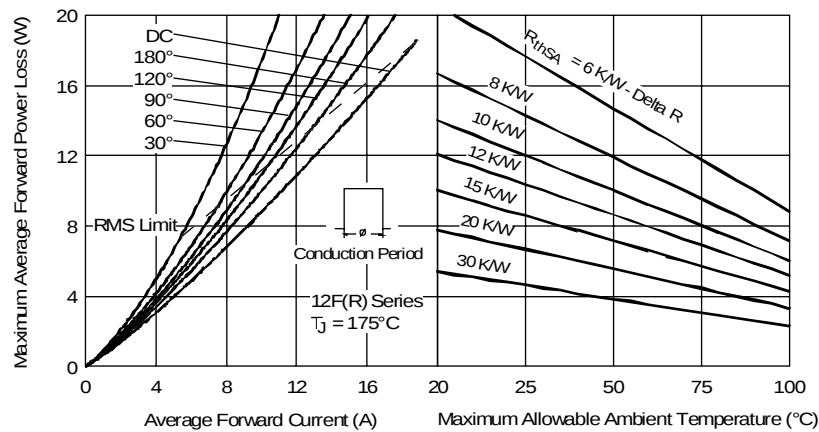


Fig. 4 - Forward Power Loss Characteristics

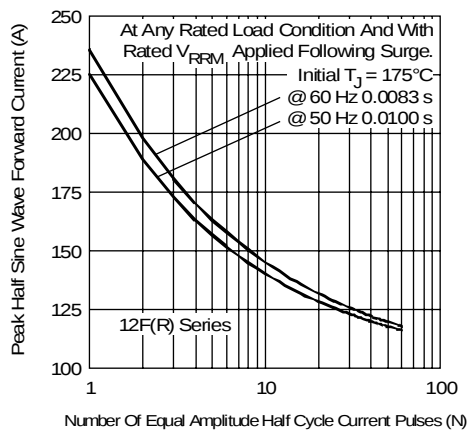


Fig. 5 - Maximum Non-Repetitive Surge Current

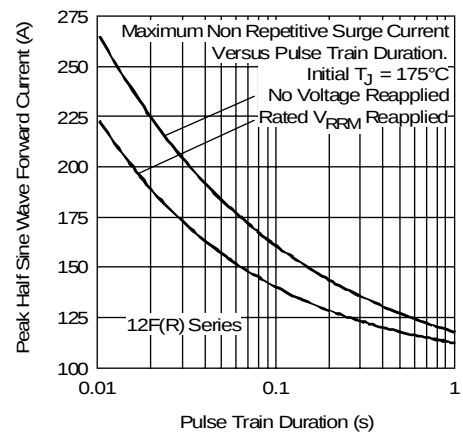


Fig. 6 - Maximum Non-Repetitive Surge Current

12F(R) Series

Bulletin I20205 rev. A 09/98

International
IR Rectifier

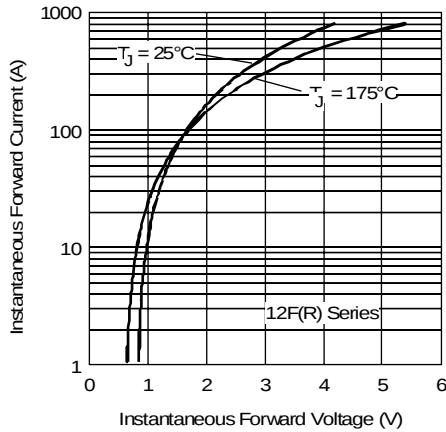


Fig. 7 - Forward Voltage Drop Characteristics

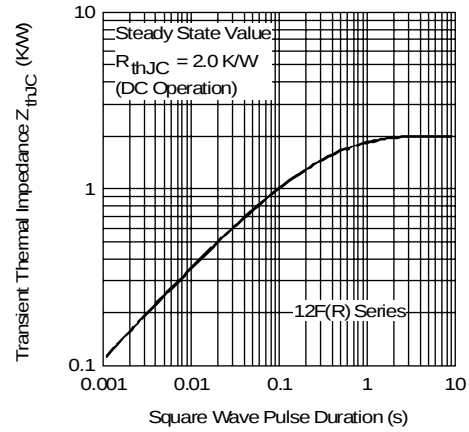


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

International
IR Rectifier

WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245 U.S.A. Tel: (310) 322 3331. Fax: (310) 322 3332.
EUROPEAN HEADQUARTERS: Hurst Green, Oxted, Surrey RH8 9BB, U.K. Tel: ++ 44 1883 732020. Fax: ++ 44 1883 733408.
IR CANADA: 15 Lincoln Court, Brampton, Markham, Ontario L6T3Z2. Tel: (905) 453 2200. Fax: (905) 475 8801.
IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg. Tel: ++ 49 6172 96590. Fax: ++ 49 6172 965933.
IR ITALY: Via Liguria 49, 10071 Borgaro, Torino. Tel: ++ 39 11 4510111. Fax: ++ 39 11 4510220.
IR FAR EAST: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo, Japan 171. Tel: 81 3 3983 0086.
IR SOUTHEAST ASIA: 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994. Tel: ++ 65 838 4630.
IR TAIWAN: 16 Fl. Suite D.207, Sec. 2, Tun Haw South Road, Taipei, 10673, Taiwan. Tel: 886 2 2377 9936.

<http://www.irf.com>

Fax-On-Demand: +44 1883 733420

Data and specifications subject to change without notice.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9